

FORM PTO-1449		ATTY. DOCKET NO. 200310842-1	APPLICATION NO.	CONFIRMATION NO.
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		APPLICANT P t r J. Fricke et al.		
(Use several sheets if necessary)		FILING DATE 02-04-2004	GROUP	

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
On	1A	20030189851A	10-09-2003	Brandenberger et al.	
	1B	20030185048A	10-02-2003	Fricke et al.	
	1C	20030178693A	09-25-2003	Bhattacharyya et al.	
	1D	20030161175A	08-28-2003	Fricke et al.	
	1E	20030151948A	08-14-2003	Bhattacharyya	
	1F	20030081446A	05-01-2003	Fricke et al.	
	1G	20030072126A	04-17-2003	Bhattacharyya	
	1H	6,549,447-B	04-15-2003	Fricke et al.	
	1I	20030042534A	03-06-2003	Bhattacharyya	
	1J	20020028541A	03-07-2002	Lee et al.	
On	1K	6,344,373-B	02-05-2002	Bhattacharyya et al.	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	1L					
	1M					
	1N					
	1O					
	1P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

On	1Q	DIMARIA et al., "Enhanced conduction and minimized charge trapping in electrically alterable read-only memories using off-stoichiometric silicon dioxide films" J. Appl. Phys. 55 (8), 15 Apr 1984, pp. 3000-3019
On	1R	DIMARIA et al., "Enhanced storage dynamic cell using composite silicon-rich SiO ₂ and thermal SiO ₂ layers" IBM Tech. Disc. Bull., Mar. 1984, pp. 5380-5383
On	1S	DIMARIA et al., "Use of composite silicon-rich SiO ₂ / and SiO ₂ / layers or off-stoichiometric CVD SiO ₂ / layers for improvement of poly 1 to poly 2 dielectric" IBM Tech. Disc. Bull., May 1983, p. 6417

EXAMINER	DATE CONSIDERED
On	9/4/05

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REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
ON	1A	5,811,870-B	09-22-1998	Bhattacharyya et al.	
	1B	5,617,351-B	04-01-1997	Bertin et al.	
	1C	5,481,128-B	01-02-1996	Hong	
	1D	5,468,663-B	11-21-1995	Bertin et al.	
	1E	5,451,535-B	09-19-1995	Chan et al.	
	1F	5,331,189-B	07-19-1994	Chan et al.	
	1G	5,298,447-B	03-29-1994	Hong	
	1H	4,752,812-B	06-21-1988	Arienzo et al.	
	1I	4,688,078-B	03-18-1987	Hsieh	
	1J	4,471,471-B	09-11-19	DiMaria	
ON	1K	4,446,535-B	05-01-1984	Gaffney et al.	

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	1L					
	1M					
	1N					
	1O					
	1P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

ON	1Q	H. CHAO "Electrically alterable read-only memory array" IBM Tech. Disc. Bull., June 1982, pp. 41-43
ON	1R	DIMARIA et al., "Electrically-Alterable Memory Using A Dual Electron Injector Structure," Electron Dev. Lett., EDL-1 (9), Sept. 1980, pp. 179-181
ON	1S	DIMARIA et al. "Two carrier dual injector structur , IBM Tech. Disc. Bull., Aug 1980, pp. 1277-1279

EXAMINER	DATE CONSIDERED
ON	9/4/08

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REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
ON	1A	4,432,072-B	02-14-1984	Chao et al.	
ON	1B	4,363,110-B	12-07-1982	Kalter et al.	
1C					
1D					
1E					
1F					
1G					
1H					
1I					
1J					
1K					

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	1N					
	1O					
	1P					

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ON	1Q	DIMARIA et al. "Dual electron injector structure" Appl. Phys. Lett. 37(1), 1 Jul. 1980, pp. 61-64
ON	1R	DIMARIA et al. "High current injection into SiO ₂ from Si rich SiO ₂ films and experimental applications," J. Appl. Phys., 51(5), May 1980, pp. 2722-2735
ON	1S	DIMARIA et al., "High current injection into SiO ₂ using Si-rich SiO ₂ films and experimental applications," in "The Physics of MOS Insulators" (G. Lucovsky et al., Eds.) Pergamon Press, New York, 1980

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9/4/05